

ABSTRACT

There is provided an organic thin film transistor comprising: an organic substrate; a gate electrode; a gate insulating film; an organic semiconductor film; a source electrode; and a drain electrode, and in the organic thin film transistor, an average surface roughness Ra of the gate electrode which is in contact with the gate insulating film is 0.1 nm to 15 nm. The organic thin film transistor provides a stable performance characteristic even when a conductor film provided on a substrate whose shape is unstable and whose flatness is low as compared with a silicon wafer, such as a substrate made of a glass epoxy resin, is used as a gate electrode.